

Public Products List

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PCN Title: BOM Changes (LF plating and DA) on selected VIPER products (TFME subcon as assy plant).

PCN Reference: AMS/22/13142

Subject: Public Products List

Dear Customer,

Please find below the Standard Public Products List impacted by the change.

VIPER37LE	VIPER38LE	VIPER38HE
VIPER37HE		

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Reliability Report

Product Line MT19 (UI01 + ZP82)

Product Description Off-line Converter

Package SDIP10

Silicon Technology

Supermesh (ZP82)

Traceability					
Diffusion Plant	Catania Ang Mo Kio (Singapore)				
Assembly Plant	TFME				
Reliabi	lity Assessment				
Pass 🖂					
Fail					

Note: this report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the electronic device conformance to its specific mission profile. This report and its contents shall not be disclosed to a third party without previous written agreement from STMicroelectronics or under the approval of the author (see below).

Version	Content description	Date	Author	Function
1.0	Initial Revision	21-Sep-21	P. Teruzzi/G. Capodici	Reliability Engineer

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Quality & Reliability - AMS Group Reliability Evaluation Report

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1 RELIABILITY EVALUATION OVERVIEW

1.1 Objective

MT19 is an already qualified device. This report contains the reliability evaluation of MT19 device diffused in Catania/Ang Mo Kio and assembled in SDip10 in TFME, in the overall plan of 8200T Glue and SDIP10LB(S-Ag) with Cu Ring lead frame qualification including also other test vehicle.

1.2 Reliability Strategy

Reliability trials performed as part of this reliability evaluation are in agreement with **ST 0061692** specification and are listed in below Test Plan. For details on test conditions, generic data used and specifications references, refer to test results summary in section 3.

1.3 Conclusion

All reliability tests have been completed with positive results. Neither functional nor parametric rejects were detected at final electrical testing.

Based on the overall results obtained, MT19 device diffused in Catania/Ang Mo Kio and assembled in SDip10 in TFME, has positively passed reliability evaluation.

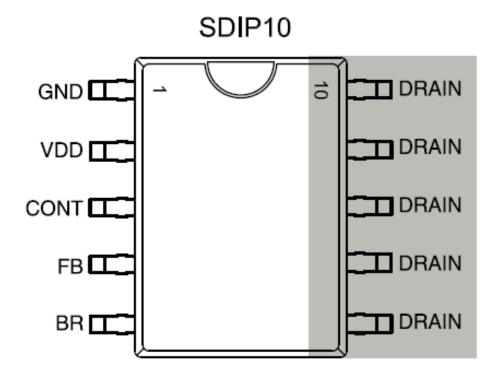


2 PRODUCT OR TEST VEHICLE CHARACTERISTICS

2.1 Generalities

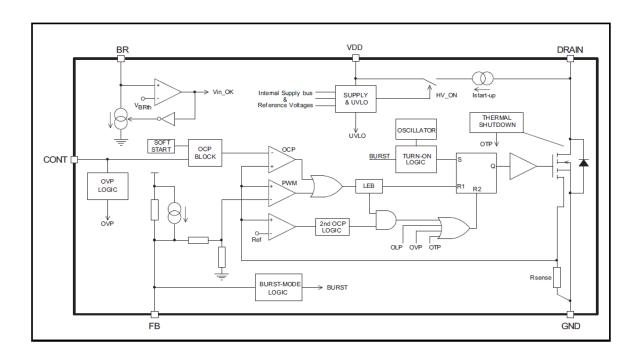
This device is an offline converter with an 800 V rugged power section, a PWM control, two levels of overcurrent protection, overvoltage and overload protection, hysteretic thermal protection, soft-start, and safe auto-restart after the removal of any fault condition.

2.2 Pin connection



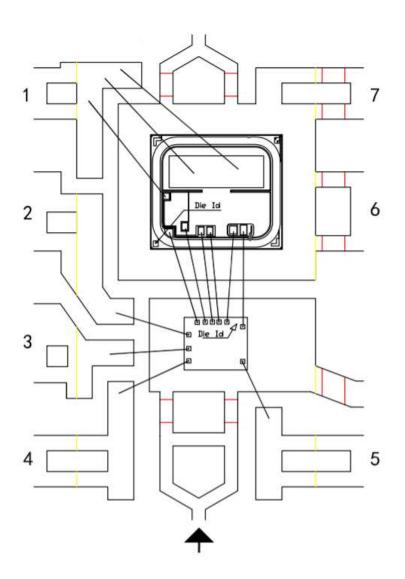


2.3 Block diagram



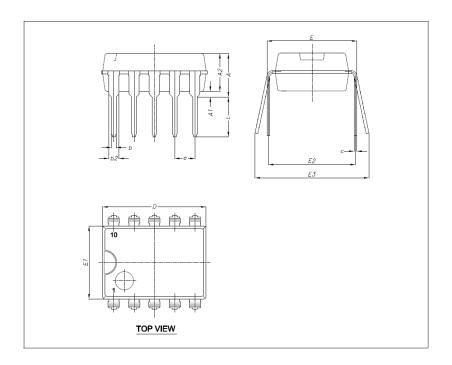


2.4 Bonding diagram





2.5 Package Outline / Mechanical data



Dim.		mm	
Dim.	Min.	Тур.	Max.
Α			5.33
A1	0.38		
A2	2.92		4.95
b	0.36		0.56
b2	0.51		1.15
С	0.2		0.36
D	9.02		10.16
E	7.62		8.26
E1	6.1		7.11
E2		7.62	
E3			10.92
е		1.77	
L	2.92		3.81



2.6 Traceability

2.6.1 Wafer fab information

Table 1

Wafer fab information				
UIO1				
Wafer fab name / location	CATANIA			
Wafer diameter (inches)	8			
Die thickness (µm)	725			
Silicon process technology	BCD6			
Die finishing front side (passivation)	TEOS/SiN/Polymide			
Die finishing back side	RAW SILICON			
Die area (X,Y) (µm)	1320,1112			
Metal levels	3			
Bond Pad Material	Ti/AlCu/TiNARC			

Table 2

14014					
Wafer fab information					
ZP82					
Wafer fab name / location	Ang Mo Kio - Singapore				
Wafer diameter (inches)	6				
Die thickness (µm)	280				
Silicon process technology	Supermesh				
Die finishing front side (passivation)	SiN (nitride)				
Die finishing back side	Ti/Ni/Au				
Die area (X,Y) (µm)	2830,2640				
Metal levels	1				
Bond Pad Material	AlSi				

2.6.2 Assembly information

Table 3

Assembly Information					
DIP7					
Assembly plant name	TFME				
Lead frame finishing (material)	Sn				
Die attach material	8200T				
Wire bonding material/diameter	Au / 1.0 mil				
Molding compound material	EMG-400-1F (HHCK)				



2.6.3 Reliability information

Table 4

Reliability Information				
Deliability laboratory name / legation	Agrate-Cornaredo / Italy (lot 1,2,3,7)			
Reliability laboratory name / location	Muar / Malaysia (lot 4,5,6)			

Note: ST is ISO 9001 certified. This induces certification of all internal and subcontractor labs. ST certification document can be downloaded under the following link: http://www.st.com/content/st_com/en/support/quality-and-reliability/certifications.html



3 TESTS RESULTS SUMMARY

3.1 Lot Information

Table 5

Lot #	Diffusion Lot Trace code	Die Revision (Cut)	Raw Line	Package	Note
1	<mark>V584258M</mark>	BE6	FEJG*MV61BE6	DIP7	Equivalent Test vehicle
2	V5840WY9	BG6	RFJG*MV34BG6	DIP7	Equivalent Test vehicle
3	<mark>V5819UU6</mark>	AEX	FU(E*MT19AEX	SDIP10	Equivalent Test vehicle
4	V5030UYW	AEX	3U(E*MT19AEX	SDIP10	
5		AEX	FU)E*MT19AEX	DIP7	Equivalent Test vehicle



3.2 Test plan and results summary

<u>Table 6</u> – ACCELERATED LIFETIME SIMULATION TESTS

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results/Lot Fail/S.S.	Comments: (N/A =Not Applicable)
HTOL		VCC=23V TJ=150°C Duration= 1000hrs □ After PC ☑ Testing at Room	3	45	135	Lot 1: 0 / 45 Lot 2: 0 / 45 Lot 3: 0 / 45	
HTRB		VDRAIN=640V VCC=23V TJ=150°C Duration= 1000hrs □ After PC ☑ Testing at Room	3	45	135	Lot 1: 0 / 45 Lot 2: 0 / 45 Lot 3: 0 / 45	

Note: Test method revision reference is the one active at the date of reliability trial execution.



Table 7 - ACCELERATED ENVIRONMENT STRESS TESTS

Note: Test method revision reference is the one active at the date of reliability trial execution.



Table 8 - ELECTRICAL VERIFICATION TESTS

Test code	Stress method	Stress Conditions	Lots	S.S.	Total	Results Fail/S.S.	Comments: (N/A =Not Applicable)
CDM	ANSI/ESD STM	CDM=+/-1500V ⊠ Testing at Room	1	3	3	Lot 3 :0 / 3	
НВМ	ANSI/ESDA/JEDEC	HBM=+/-4000V ☑ Testing at Room	1	3	3	Lot 5 :0 / 3	
LU	JESD78	Current Injection Class II - Level B (+/- 100mA) Overvoltage Class II - Level B (1,5 x Vmax) □ Testing at Room	1	6	6	Lot 5 :0 / 6	

Note: Test method revision reference is the one active at the date of reliability trial execution.





4 APPLICABLE AND REFERENCE DOCUMENTS

Reference	Short description
AEC-Q100	Failure Mechanism Based Stress Test Qualification for Integrated Circuits in automotive applications
JESD47	Stress-Test-Driven Qualification of Integrated Circuits
DMS 0061692	Reliability Tests and Criteria for Product Qualification



5 **GLOSSARY**

List update based on applicable items.

ACBV	Autoclave	MR	Multiple Reflow
	AC Blocking Voltage	MS	Mechanical Shock
ASER	Accelerated Soft Error Rate	MSeq	Mechanical sequence
AST	Adhesion Shear Test	MSL	Moisture Sensitivity Level
BI	Burn-In	NVM	Non Volatile Memory
BT3P	Board 3 points Bending Test	PC	Preconditioning
BT4P	Board 4 points Bending Test	PD	Physical Dimensions
CA	Constant Acceleration	PTC	Power Temperature Cycling
CDM	Electrostatic Discharge - Charged Device Model	RS	Repetitive Surge Test
ConA	Construction Analysis	TSH	Resistance to Solder Heat
CVS	Constant Voltage Stress	RTSER	Real-Time Soft Error Rate
DBT	Dead Bug Test	SAM	Scanning Acoustic Microscopy
DPA	Destructive Physical Analysis	SBP	Solder Ball Pull
DROP	Package drop	SBS	Solder Ball Shear
DS	Die Shear	SC	Short Circuit Characterization
DToB	Drop Test on Board	SCCSS	Smartcard - Constant Supply Stress
EDR	NVM Program/Erase Endurance & Data Retention Stress Test	SCMCMS	Smartcard - MasterCard Mechanical Stress
ELFR	Early Life Failure Rate	SCMF	Smartcard - Magnetic Field Stress
EMC	<u>'</u>	SCPOOS	Smartcard - Power Off/On Stress
	Electromagnetic Compatibility	SCRFC	Smartcard - RF On/Off Cyclic Stress
EOS	Electrical Overstress characterization	SCRFS	Smartcard - RF On Static Stress
ESeq	Environmental sequence	ScrT	Screw Test
EV	External Visual	SCSA	Smartcard - Salt Atmosphere
GFF GFL	Gross/Fine Leak	SCUV	Smartcard - UV Test
GL	Electro-thermally Induced Gate Leakage	SCXRAY	Smartcard - XRAY Test
GStress	Gate Stress	SD	Solderability
GUN	Electrostatic Discharge – System Level Test	SSOP	Steady State Operational
H3TRB	High Humidity High Temperature Reverse Bias	SToB	Shock Test on Board
HAST	Biased HAST (Highly Accelerated Stress Test)	TC	Temperature Cycling
НВМ	Electrostatic Discharge – Human Body Model	TCDT	Temperature Cycling Delamination Test
HER	Hermeticity	TCHT	Temperature Cycling Hot Test
НММ	Electrostatic Discharge – Human Metal Model	ТСоВ	Temperature Cycling on Board
HTFB	High Temperature Forward Bias	ТНВ	Temperature Humidity Bias
HTGB	High Temperature Gate Bias	THS	Temperature Humidity Storage
НТННВ	High Temperature High Humidity Bias	TLP	Electrostatic Discharge - Transmission Line Pulse
HTOL	High Temperature Operating Life	TS	Thermal Shocks
HTRB	High Temperature Reverse Bias.	TStr	Terminal Strength
HTSL	High Temperature Storage Life	Tumb	Tumbler Test
IOL	Intermittent Operating Life	UHAST	Unbiased HAST (Highly Accelerated Stress Test)
IWV	Internal Water Vapor	VToB	Vibration Test on Board
LF	Lead Free	VFV	Variable Frequency Vibration
LI	Lead Integrity	WAT	Tin (Sn) Whisker Acceptance Testing
LT	Lid Torque	WBI	Wire Bond Integrity
LTOL	Low Temperature Operating Life	WBP	Wire Bond Pull
LTSL	Low Temperature Storage Life	WBS	Wire Bond Shear
LU	Latch-Up	WBSt	Wire Bond Strength
MM	Electrostatic Discharge – Machine model	XRAY	X ray inspection



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